

Title (en)  
LIGHT EMITTING DIODE CHIP

Title (de)  
LED-CHIP

Title (fr)  
PUCE À DIODE ÉLECTROLUMINESCENTE

Publication  
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Application  
**EP 21199362 A 20110613**

Priority  

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Abstract (en)  
Exemplary embodiments of the present invention provide light emitting diode (LED) chips and a method of fabricating the same. An LED chip according to an exemplary embodiment includes a substrate; a light emitting structure arranged on the substrate, and an alternating lamination bottom structure arranged under the substrate. The alternating lamination bottom structure includes a plurality of dielectric pairs, each of the dielectric pairs including a first material layer having a first refractive index and a second material layer having a second refractive index, the first refractive index being greater than the second refractive index.

IPC 8 full level  
**G02B 1/10** (2015.01); **G02B 5/08** (2006.01); **H01L 33/00** (2010.01); **H01L 33/32** (2010.01); **H01L 33/46** (2010.01); **G02B 5/28** (2006.01); **H01L 33/08** (2010.01); **H01L 33/20** (2010.01); **H01L 33/50** (2010.01); **H01L 33/60** (2010.01); **H01L 33/62** (2010.01)

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C-Set (source: CN EP US)  
CN US  
1. **H01L 2224/48091 + H01L 2924/00014**  
2. **H01L 2224/73265 + H01L 2224/32245 + H01L 2224/48247 + H01L 2924/00**  
EP  
1. **H01L 2224/48091 + H01L 2924/00014**  
2. **H01L 2224/73265 + H01L 2224/32245 + H01L 2224/48247 + H01L 2924/00012**

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